

# NOT RECOMMENDED FOR NEW DESIGN CONTACT US



BSS126SK

#### N-CHANNEL DEPLETION MODE MOSFET

### **Product Summary**

BV <sub>DSX</sub>	R <sub>DS(ON)</sub> Max	IDSS Min TA = +25°C
600V	700Ω @ V <sub>GS</sub> = 0V	7mA

#### **Features and Benefits**

- N-Channel
- ESD Protected
- Depletion Mode
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

### **Description and Applications**

This new generation uses advanced planar technology MOSFET, provide excellent high voltage and fast switching, making it ideal for small-signal and level shift applications.

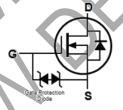
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

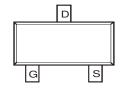
#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)









Top View Equivalent Circuit

Top View

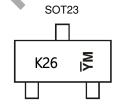
### Ordering Information (Note 4)

Part Number	Case	Packaging
BSS126SK-7	SOT23	3000/Tape & Reel
BSS126SK-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



K26 = Product Type Marking Code YM = Date Code Marking  $\overline{Y}$  = Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н		J	K	L	М	N	0	Р	R	S	Т
Month	la.	Fab	Mar	A	May	live	l. d	A	Con	Oct	Nov	Doo
MOUTH	Jan	Feb	Iviar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	600	V		
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	30 24	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	35 28	mA
Continuous Source Current (Note 5) V <sub>GS</sub> = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	Is	30 24	mA
Continuous Source Current (Note 6) V <sub>GS</sub> = 10V	Is	35 28	mA		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	I <sub>DM</sub>	0.09	Α		
Pulsed Source Current (10µs Pulse, Duty Cycle =	1%)		I <sub>SM</sub>	0.09	A

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation, @T <sub>A</sub> = +25°C (Note 5)	PD	1	W
Thermal Resistance, Junction to Ambient @TA = +25°C (Note 5)	Reja	124.7	°C/W
Power Dissipation, @T <sub>A</sub> = +25°C (Note 6)	P <sub>D</sub>	1.3	W
Thermal Resistance, Junction to Ambient @TA = +25°C (Note 6)	R <sub>θ</sub> ЈА	95.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSX</sub>	600			V	$V_{GS} = -5V$ , $I_{D} = 250\mu A$	
Drain-Source Cutoff Current	I <sub>D</sub> (OFF)	-	+	0.1	μΑ	V <sub>GS</sub> = -5V, V <sub>DS</sub> = 600V	
Gate-Source Leakage	lgss	4	1	±10	μΑ	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-2.7	-2.2	-1.4	V	$V_{DS} = 3V$ , $I_D = 8\mu A$	
On-State Drain Current	IDSS	7			mA	$V_{GS} = 0V$ , $V_{DS} = 25V$	
Static Drain-Source On-Resistance	Proven		111	500	Ω	$V_{GS} = 10V, I_D = 16mA$	
Static Drain-Source On-Nesistance	R <sub>DS(ON)</sub>	7	101	700	12	$V_{GS} = 0V$ , $I_D = 3mA$	
Diode Forward Voltage	V <sub>SD</sub>		0.7	1.3	V	$V_{GS} = -5V$ , $I_{S} = 16mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		30.9				
Output Capacitance	Coss	_	4.2	_	pF	V <sub>G</sub> S = -5V, V <sub>D</sub> S = 25V, f = 1MHz	
Reverse Transfer Capacitance	Crss	_	0.8	_			
Gate Resistance	Rg	_	121	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	-	2			$V_{DD} = 400V$ ,	
Gate-Source Charge	Qgs	_	0.03	_	nC	I <sub>D</sub> = 10mA,	
Gate-Drain Charge	Qgd	_	1.7	_		$V_{GS} = -3V$ to $5V$	
Turn-On Delay Time	td(ON)	_	5.2	_	ns	V 000V	
Turn-On Rise Time	t <sub>R</sub>	_	17	_	ns	$V_{DD} = 300V$ ,	
Turn-Off Delay Time	tD(OFF)	_	67		ns	$V_{GS} = -3V$ to $7V$ , $I_{D} = 0.01A$ , $R_{G} = 6\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	873	_	ns	1D = 0.01A, ng = 022	
Reverse Recovery Time	t <sub>RR</sub>	_	164	_	ns	$V_R = -100V$ , $I_F = -1A$ , $V_{GS} = -5V$	
Reverse Recovery Charge	Qrr	_	382	_	nC	$di/dt = 100A/\mu s$	

Notes:

- 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 6. Device mounted on 1"  $\times$  1" FR-4 PCB with high coverage 2 oz. copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.



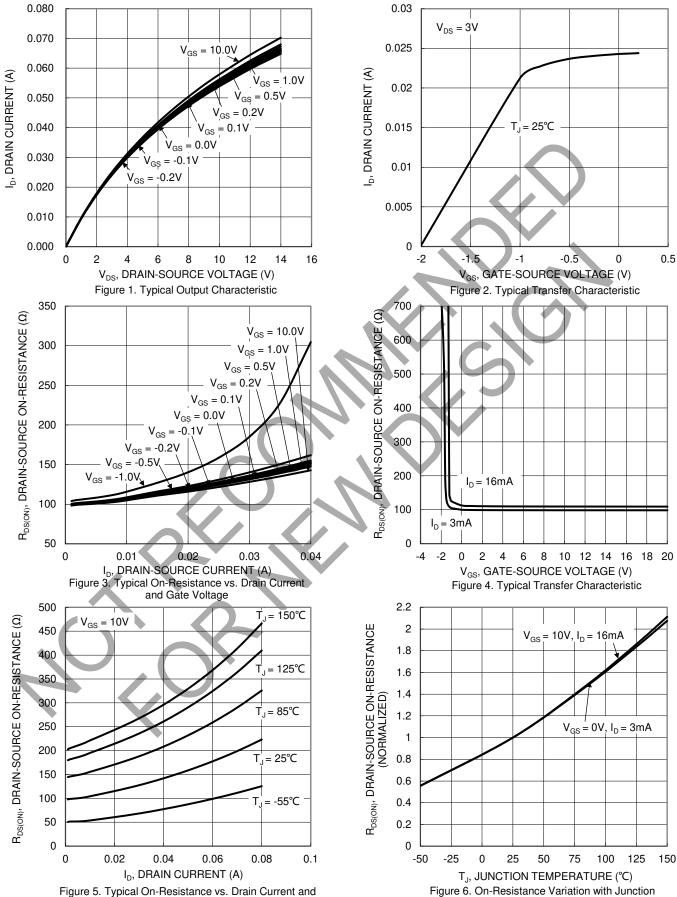


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





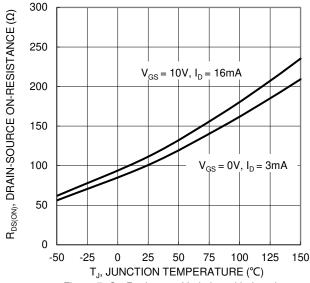


Figure 7. On-Resistance Variation with Junction Temperature

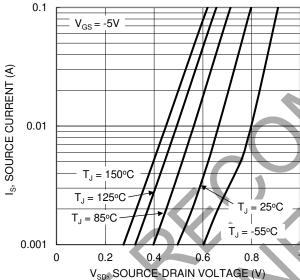


Figure 9. Diode Forward Voltage vs. Current

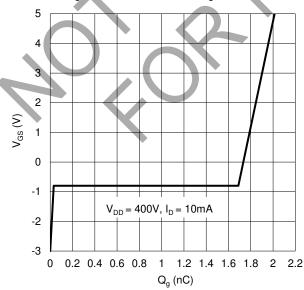
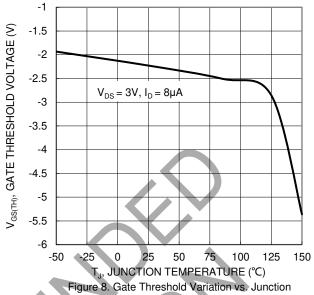


Figure 11. Gate Charge



Temperature

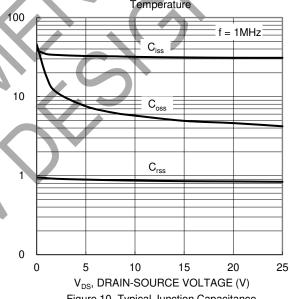


Figure 10. Typical Junction Capacitance

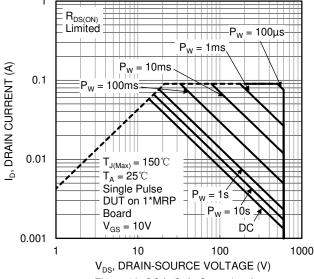


Figure 12. SOA, Safe Operation Area

UNCTION CAPACITANCE (pF)



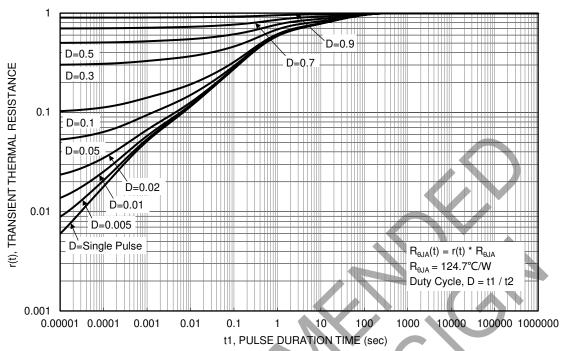


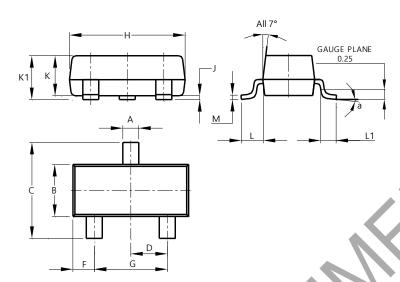
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

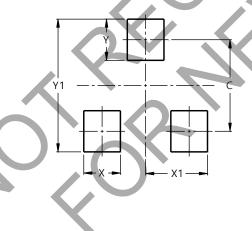


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
Ρ	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
Δ	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.





Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Υ	0.9
V1	2.0



#### IMPORTANT NOTICE

- 1. DIODES INCORPORATED AND ITS SUBSIDIARIES ("DIODES") MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
- 2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes products. Diodes products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of the Diodes products for their intended applications, (c) ensuring their applications, which incorporate Diodes products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
- 3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
- 4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
- 5. Diodes products are provided subject to Diodes' Standard Terms and Conditions of Sale (<a href="https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/">https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/</a>) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- 6. Diodes products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
- 7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
- 8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

Copyright © 2021 Diodes Incorporated

www.diodes.com